

SILICON POWER TRANSISTOR 2SD1481

NPN SILICON EPITAXIAL TRANSISTOR (DARLINGTON CONNECTION) FOR LOW-FREQUENCY POWER AMPLIFIERS AND LOW-SPEED SWITCHING

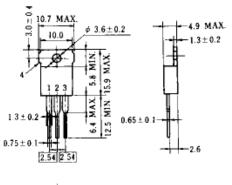
FEATURES

- On-chip C-to-B Zener diode for surge voltage absorption
- Low collector saturation voltage: VCE(SAT) = 1.5 V MAX. (at 1 A)
- Ideal for use in a direct drive from IC to the devices such as OA and FA equipment and motor solenoid relay printer head drivers

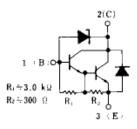
Parameter	Symbol	Ratings	Unit
Collector to base voltage	Vсво	60 ±10	V
Collector to emitter voltage	VCEO	60 ±10	V
Emitter to base voltage	VEBO	7.0	V
Collector current	IC(DC)	2.0	A
Collector current	IC(pulse)*	4.0	A
Base current	IB(DC)	0.2	А
Total power dissipation	P⊤ (Tc = 25°C)	15	W
Total power dissipation	P⊤ (Ta = 25°C)	1.5	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

PACKAGE DRAWING (UNIT: mm)







Electrode Connection

- 1. Base 2. Collector
- Collecto
 Emitter
- 4. Fin (collector)

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* PW \leq 300 μ s, duty cycle \leq 10%

ELECTRICA48CHARAGTERISTICS (Ta = 25°C)

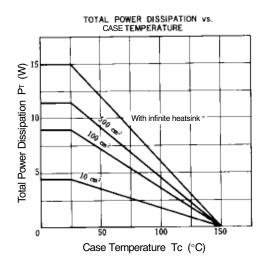
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = 40 V, I_E = 0$			1.0	μA
DC current gain	hfe1	Vce = 2.0 V, Ic = 1.0 A*	2,000		20,000	
DC current gain	hfe2	$V_{CE} = 2.0 \text{ V}, \text{ Ic} = 3.0 \text{ A}^*$	500			
Collector saturation voltage	VCE(sat)	Ic = 1.0 A, Iв = 1.0 mA*			1.5	V
Base saturation voltage	VBE(sat)	Ic = 1.0 A, Iв = 1.0 mA*			2.0	V
Turn-on time	ton	Ic = 1.0 A, IB1 = $-IB2 = 10 \text{ mA}$ RL = 50 Ω , Vcc \cong 50 V Refer to the test circuit.		0.5		μs
Storage time	tstg			2.0		μs
Fall time	tr			1.0		μs

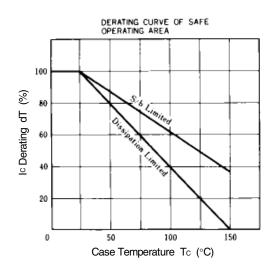
* Pulse test PW \leq 350 μ s, duty cycle \leq 2%

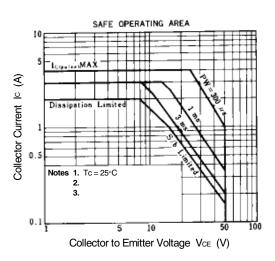
hfe CLASSIFICATION

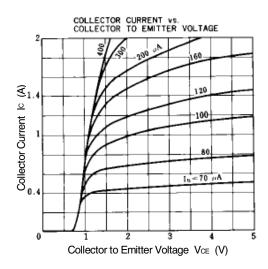
Marking	М	L	к
hfe1	2,000 to 5,000	4,000 to 10,000	8,000 to 20,000

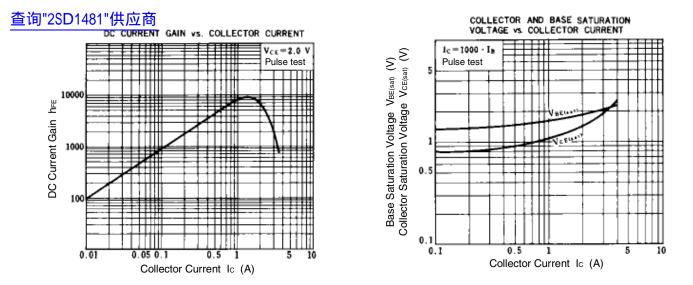
TYPICAL CHARACTERISTICS (Ta = 25°C)



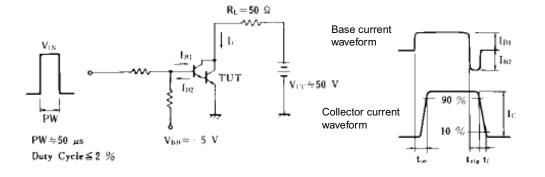








SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT



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